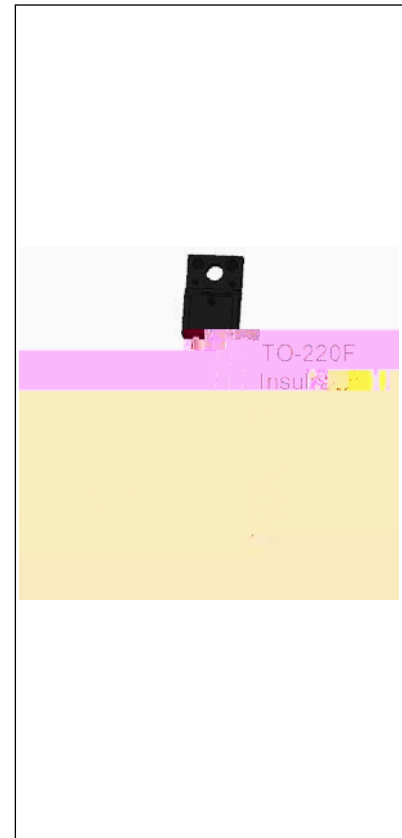




The JST06F-800CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST06F-800CW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST06F-800CW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	35/35/35	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
RMS on-state current ($T_c = 98^\circ C$)	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	65	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		72	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	21	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_a$	1 H			

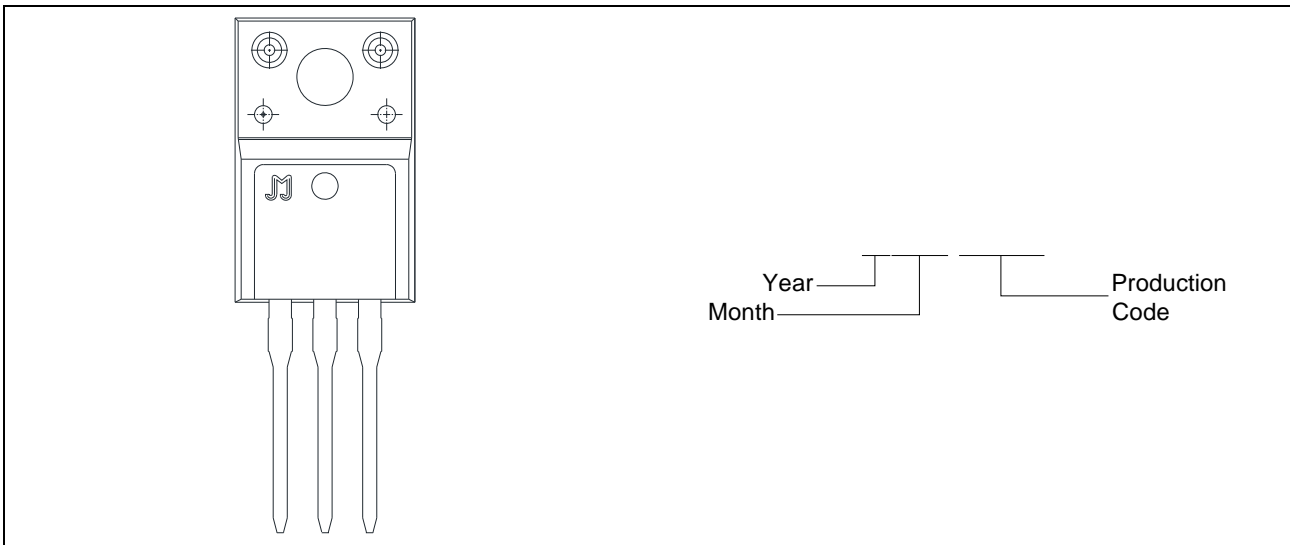
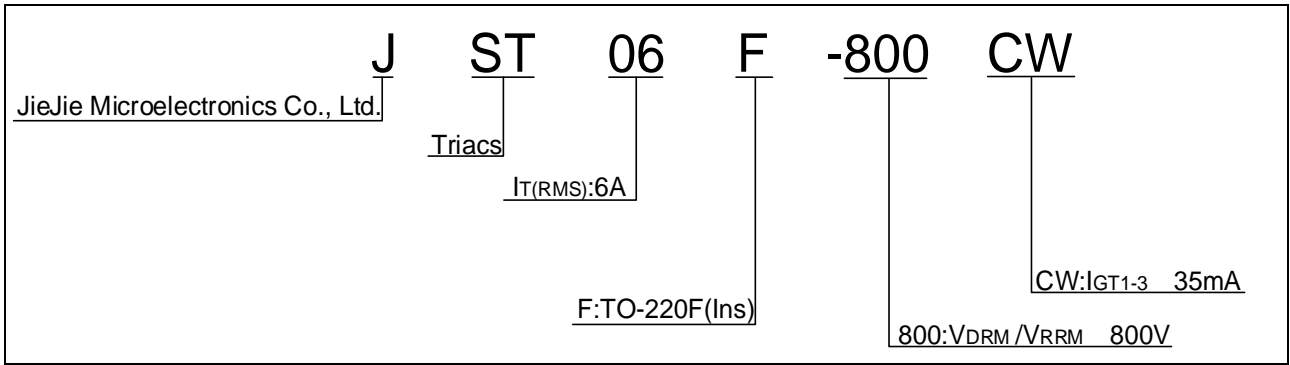


FIG.1: Maximum power dissipation versus RMS on-state current

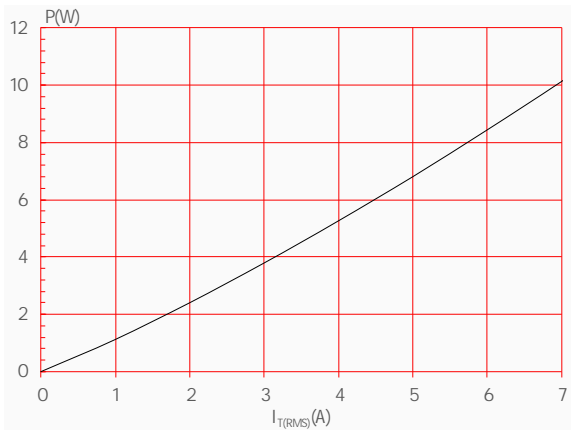


FIG.2: RMS on-state current versus case temperature

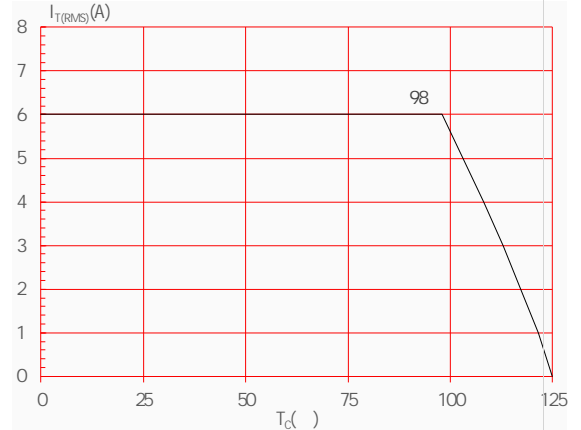


FIG.3: Surge peak on-state current versus number of cycles

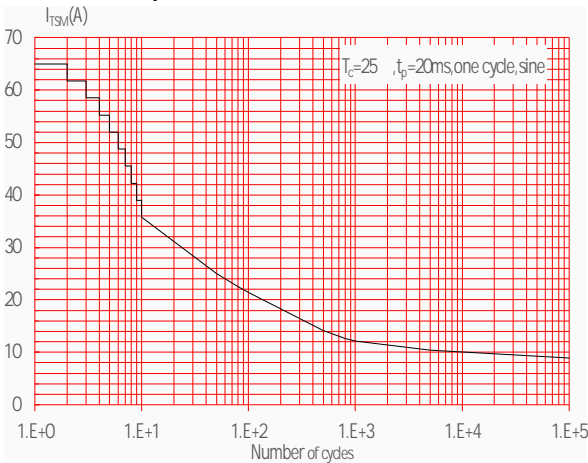


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

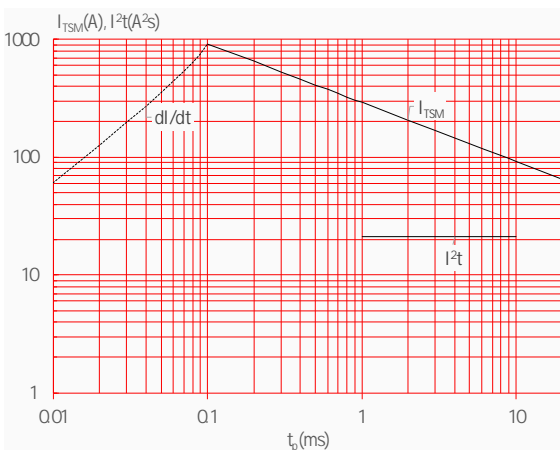


FIG.4: On-state characteristics

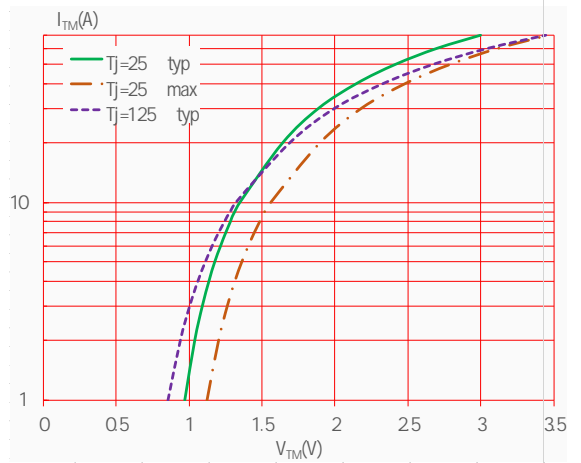


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

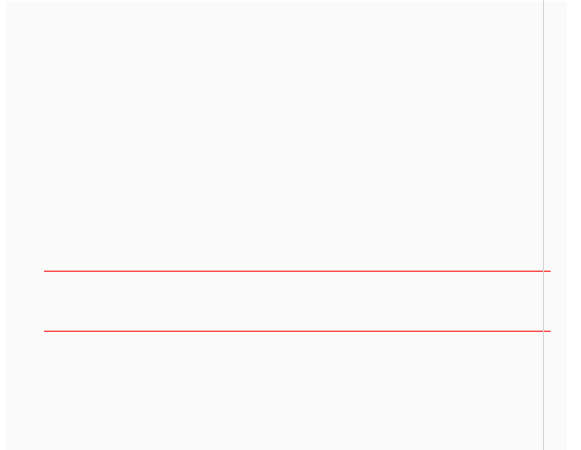
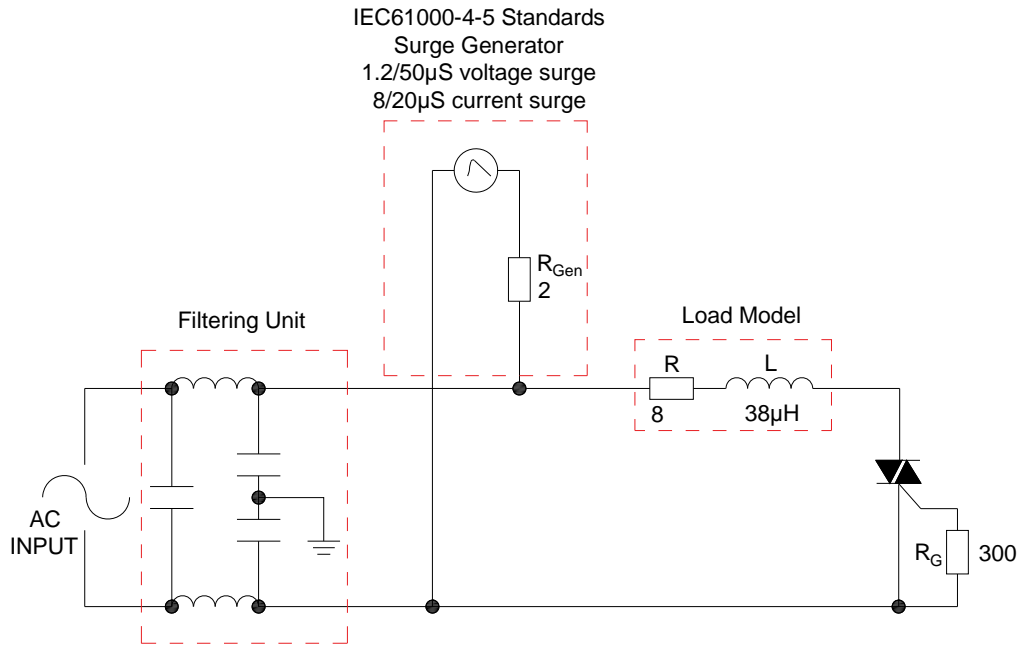
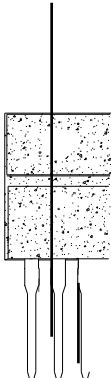


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards




Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.



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